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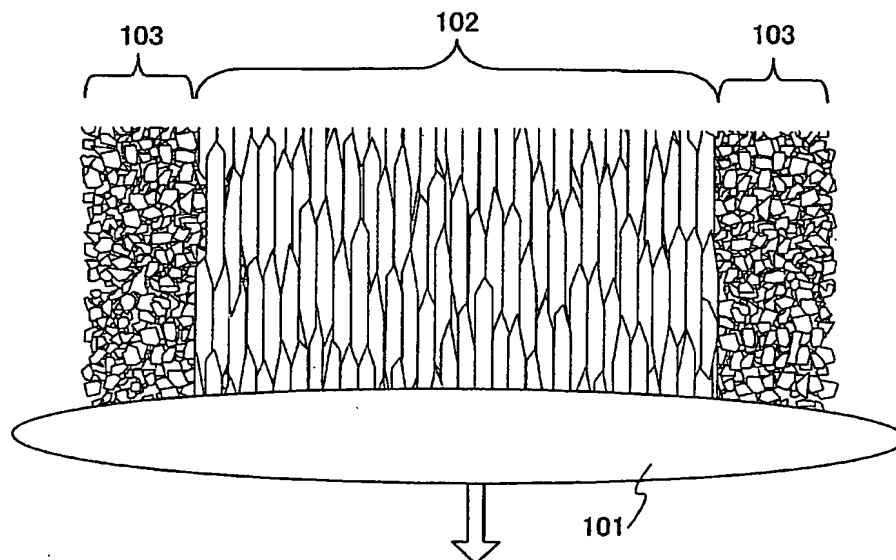
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(54) Title: SEMICONDUCTOR DEVICE



(57) Abstract: The present invention is to provide a semiconductor device that achieves high mechanical strength without reducing the circuit scale and that can prevent the data from being forged and altered illegally while suppressing the cost. The present invention discloses a semiconductor device typified by an ID chip that is formed from a semiconductor thin film including a first region with high crystallinity and a second region with the crystallinity inferior to the first region. Specifically, a TFT (thin film transistor) of a circuit requiring high-speed operation is formed by using the first region and a memory element for an identifying ROM is formed by using the second region.



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